

■ PRODUCT CHARACTERISTICS

V_{DS}	500V
$R_{DS(on)}$ Typ@ $V_{GS}=10V$	1.9 Ω
I_D	5A

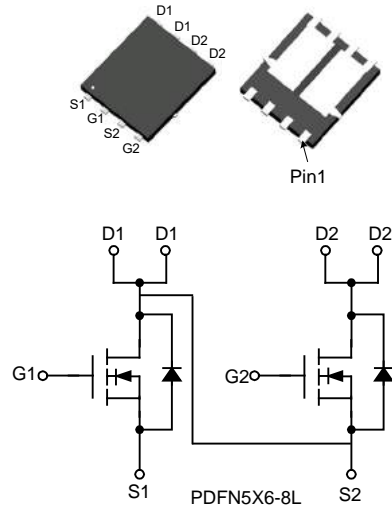
■ APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- LED power supply

■ FEATURES

- Fast switching capability
- Avalanche energy specified
- Improved dv/dt capability, high ruggedness

Symbol



■ ORDER INFORMATION

Order codes		Package	5000pieces/Reel
Halogen-free	Halogen		
N/A	MOT50221G	PDFN5X6-8L	

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	Continuous	I_D	5
	Pulsed (Note 2)	I_{DM}	13
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	151
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	P_D	50	W
Junction Temperature	T_J	+150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $L = 10mH$, $I_{AS} = 5.5A$, $V_{DD} = 50V$, $R_G = 25\Omega$ Starting $T_J = 25^\circ C$
4. $I_{SD} \leq 5.0A$, $di/dt \leq 100A/\mu s$, $V_{DD} \leq BV_{DSS}$ Starting $T_J = 25^\circ C$

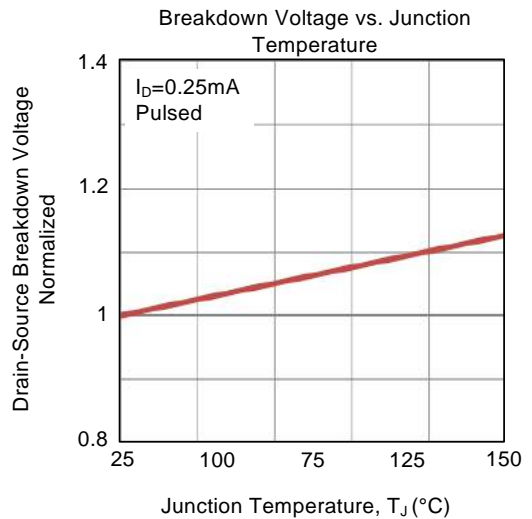
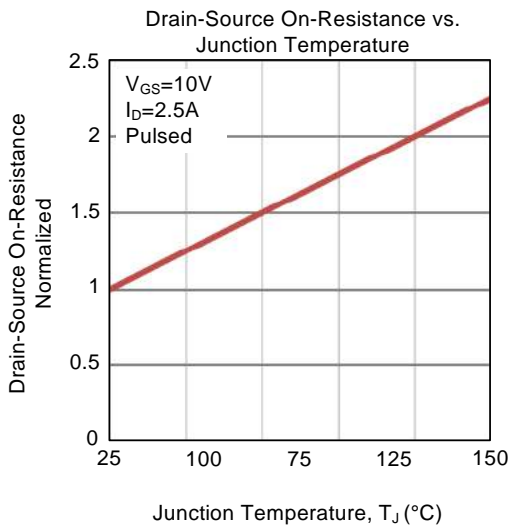
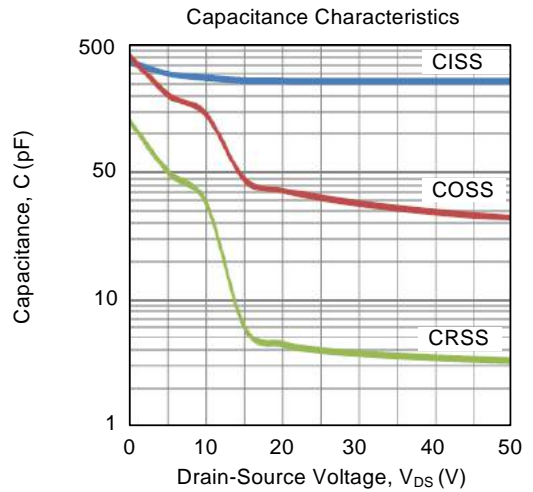
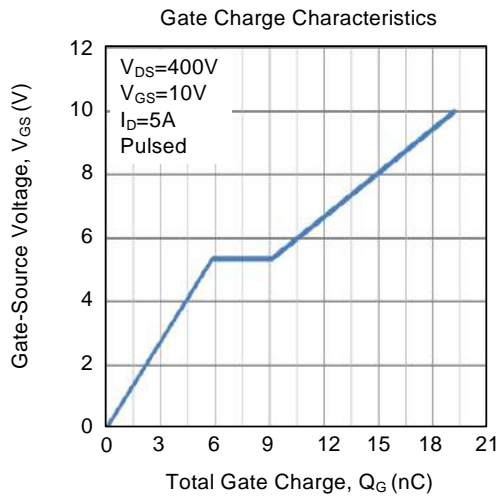
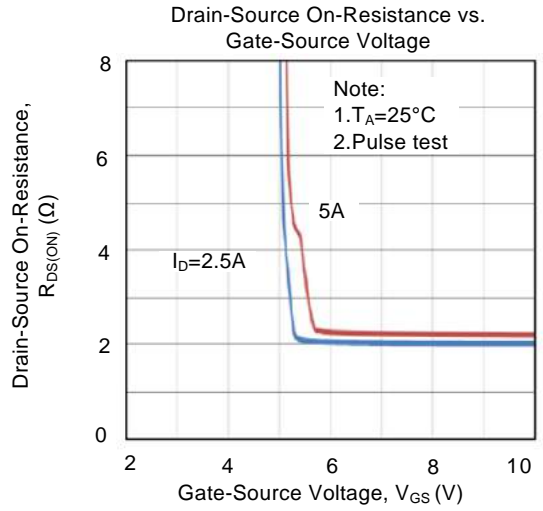
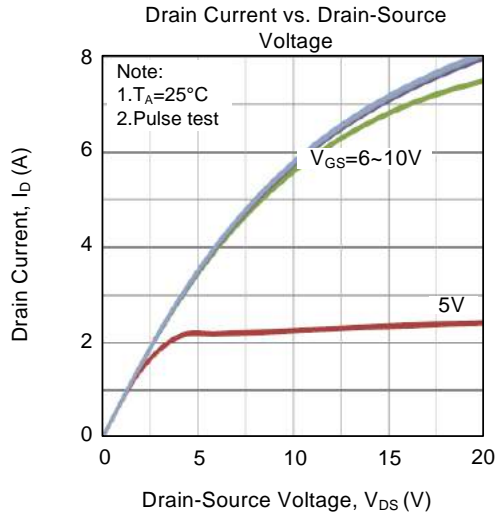
■ ELECTRICAL CHARACTERISTICS(Tc=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	500	-	-	V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C, $I_D=250\mu A$	-	0.5	-	V/°C
Drain-Source Leakage Current		I_{DSS}	$V_{DS}=500V, V_{GS}=0V$	-	-	1	μA
			$V_{DS}=400V, T_C=125^\circ C$	-	-	10	
Gate- Source Leakage Current	Forward	I_{GSS}	$V_{GS}=30V, V_{DS}=0V$	-	-	100	nA
	Reverse		$V_{GS}=-30V, V_{DS}=0V$	-	-	-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS}=10V, I_D=2.5A$	-	1.9	2.1	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	$V_{GS}=0V, V_{DS}=25V,$ $f=1.0MHz$	-	625	-	pF
Output Capacitance		C_{OSS}		-	80	-	pF
Reverse Transfer Capacitance		C_{RSS}		-	15	-	pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	$V_{GS}=10V, V_{DS}=400V,$ $I_D=5A$ (Note 1, 2)	-	18	-	nC
Gate to Source Charge		Q_{GS}		-	2.2	-	nC
Gate to Drain Charge		Q_{GD}		-	9.7	-	nC
Turn-ON Delay Time		$t_{D(ON)}$	$V_{DD}=250V, I_D=5A,$ $R_G=25\Omega$ (Note 1, 2)	-	12	-	ns
Rise Time		t_R		-	46	-	ns
Turn-OFF Delay Time		$t_{D(OFF)}$		-	50	-	ns
Fall-Time		t_F		-	48	-	ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S		-	-	5	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}		-	-	20	A
Drain-Source Diode Forward Voltage		V_{SD}	$I_S=5A, V_{GS}=0V$	-	-	1.4	V
Reverse Recovery Time		t_{rr}	$I_S=5A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$ (Note 1)	-	195	-	ns
Reverse Recovery Charge		Q_{RR}		-	0.25	-	μC

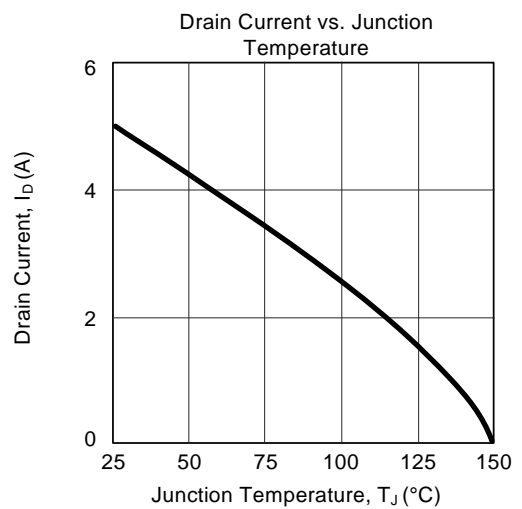
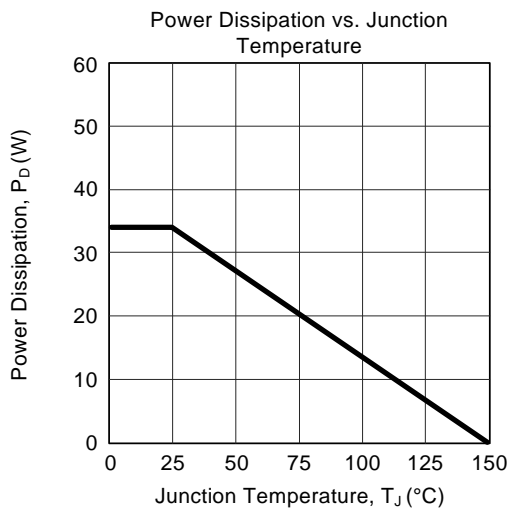
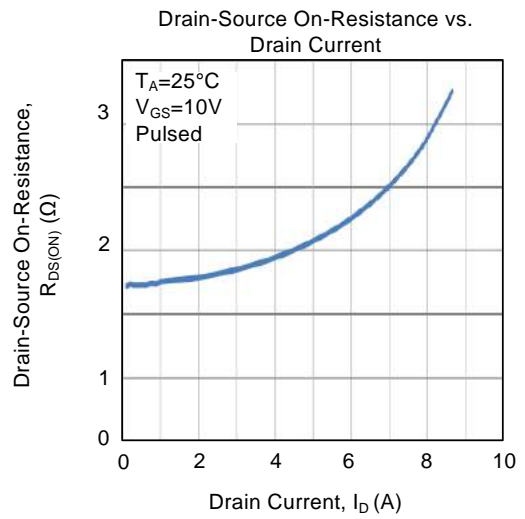
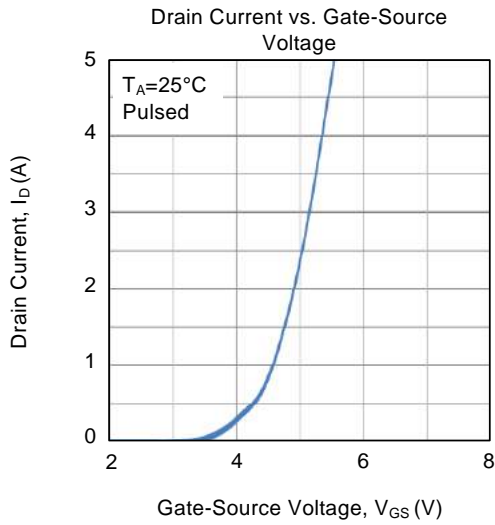
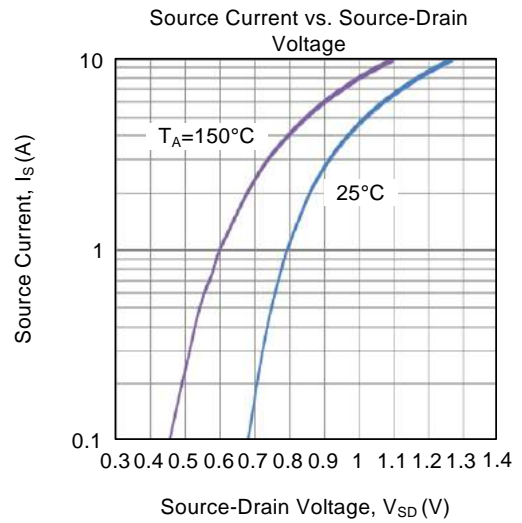
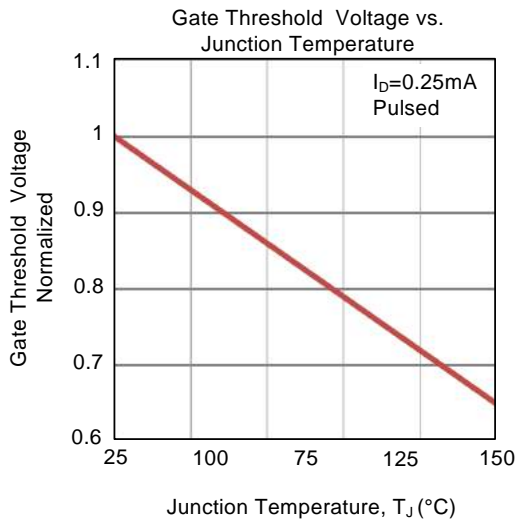
 Note: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

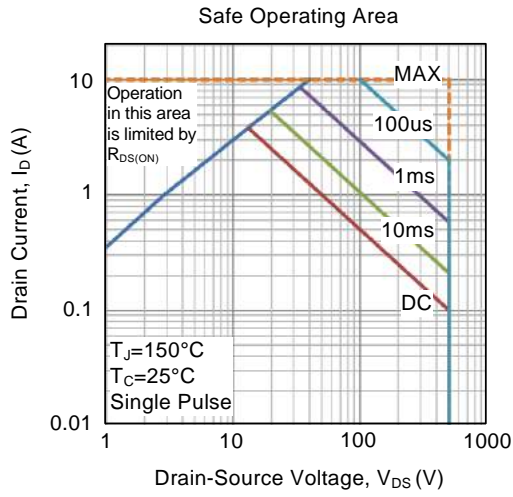
■ TYPICAL CHARACTERISTICS



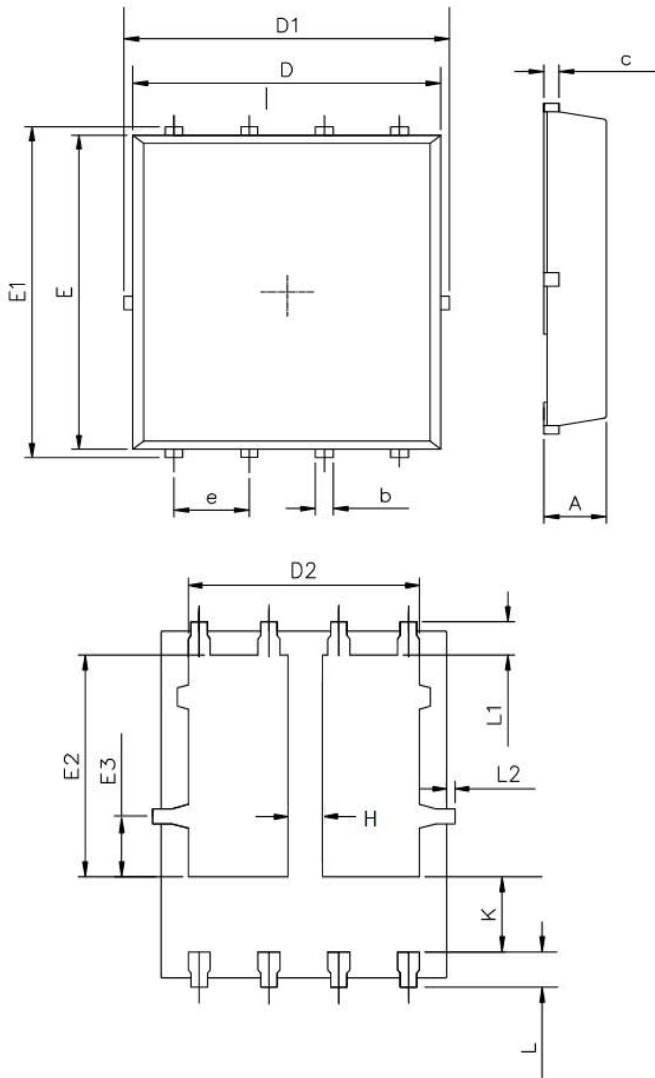
■ TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)



■ PDFN5X6-8L PACKAGE MECHANICAL DATA



UNIT: mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50
H	0.5	0.6	0.7